



《风光欣》技术资料

PCR1225

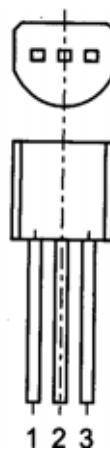
SILICON PLANAR PNP THYRISTOR

FEATURES

Current- I_{GT} : 120 μ A

I_{TRMS} : 0.6A

V_{DRM} : 400V



TO-92

1. CATHODE

2. GATE

3. ANODE

ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage	V_{TM}	$I_{TM}=0.6A$		1.6	V	
Gate trigger voltage	V_{GTF}	$V_{AK}=7V$		0.8	V	
Repetitive peak off-state voltage	V_{DRM}	$I_{CRM}=10 \mu A$, $V_{MAX}=10V$	400		V	
Holding current	I_H	$I_{HL}=20 mA$, $A_V = 7V$		5	mA	
Gate trigger current	I_{GTF}	$V_{AR}=7V$		5	15	μA
				15	30	μA
				30	45	μA
				45	60	μA
				60	80	μA
				80	120	μA